

REFERENCE DES	SIGNATION	U.S. PATENT D	OCUMENTS		
EXAMINER DOCUMENT NUMBER		DATE	NAME	CLASS/ SUBCLASS	FILING DATE
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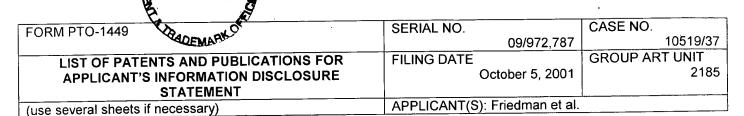
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FORM 2 2 2002

FORM 2 2 2002

SERIAL NO.

09/972,787

CASE NO.

09/972,787

FILING DATE

APPLICANT'S INFORMATION DISCLOSURE

STATEMENT

(use several sheets if necessary)

APPLICANT(S): Friedman et al.

REFERENCE	DESIG	NATION	U.S. PATEN	U.S. PATENT DOCUMENTS				
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Page 2 of 2

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FORM PTO-1449	SERIAL NO.	CASE NO.
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STATEMENT		
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